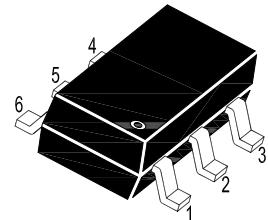
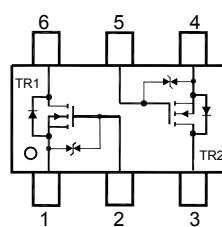


MMBT7002KDW-AH

N-Channel Enhancement Mode Field Effect Transistor

Features

- Low on resistance $R_{DS(ON)}$
- Low gate threshold voltage
- Low input capacitance
- ESD protected up to 2KV
- AEC-Q101 Qualified and PPAP Capable
- Halogen and Antimony Free(HAF), RoHS compliant



1. Source 2. Gate 3. Drain
4. Source 5. Gate 6. Drain
SOT-363 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

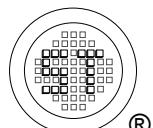
Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	60	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current (Continuous)	I_D	300	mA
Drain Current (Pulse Width $\leq 10 \mu\text{s}$)	I_{DM}	1.2	A
Total Power Dissipation	P_{tot}	$295^{1)}$ $350^{2)}$	mW
Junction and Storage Temperature Range	T_j, T_{stg}	- 55 to + 150	$^\circ\text{C}$

¹⁾ Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

²⁾ Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm^2 .

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Drain Source Breakdown Voltage at $I_D = 10 \mu\text{A}$	BV_{DSS}	60	-	V
Zero Gate Voltage Drain Current at $V_{DS} = 60 \text{ V}$	I_{DSS}	-	1	μA
Gate Source Leakage Current at $V_{GS} = \pm 20 \text{ V}$	I_{GSS}	-	± 10	μA
Gate Threshold Voltage at $V_{DS} = 10 \text{ V}, I_D = 250 \mu\text{A}$	$V_{GS(th)}$	1.1	2.1	V
Static Drain Source On-Resistance at $V_{GS} = 10 \text{ V}, I_D = 500 \text{ mA}$ at $V_{GS} = 5 \text{ V}, I_D = 50 \text{ mA}$	$R_{DS(ON)}$	- -	3 4	Ω
Forward Transconductance at $V_{DS} = 10 \text{ V}, I_D = 200 \text{ mA}$	g_{fs}	80	-	mS
Input Capacitance at $V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	C_{iss}	-	50	pF
Output Capacitance at $V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	C_{oss}	-	25	pF
Reverse Transfer Capacitance at $V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	C_{rss}	-	5	pF



MMBT7002KDW-AH

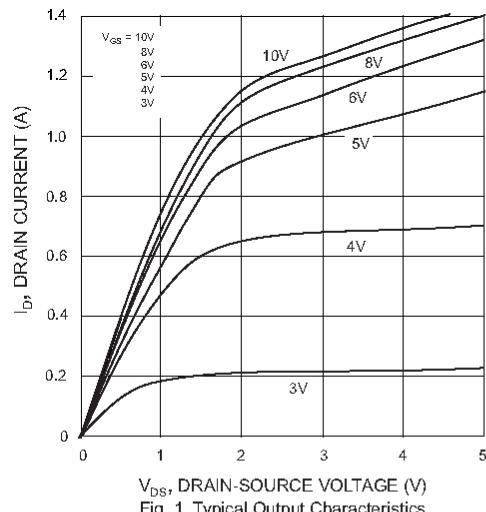


Fig. 1 Typical Output Characteristics

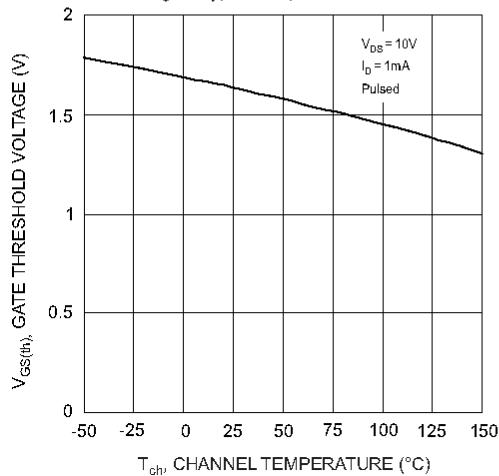


Fig. 3 Gate Threshold Voltage
vs. Channel Temperature

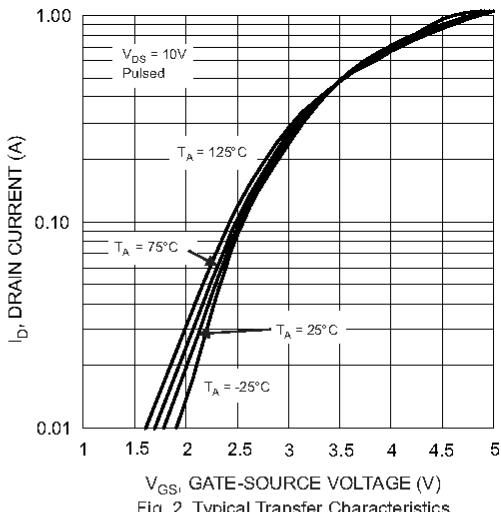


Fig. 2 Typical Transfer Characteristics

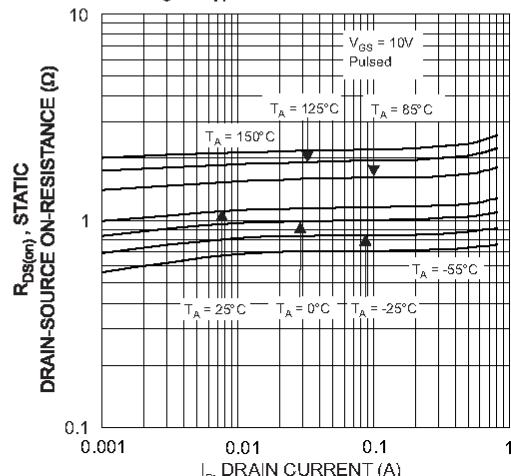


Fig. 4 Static Drain-Source On-Resistance
Vs. Drain Current

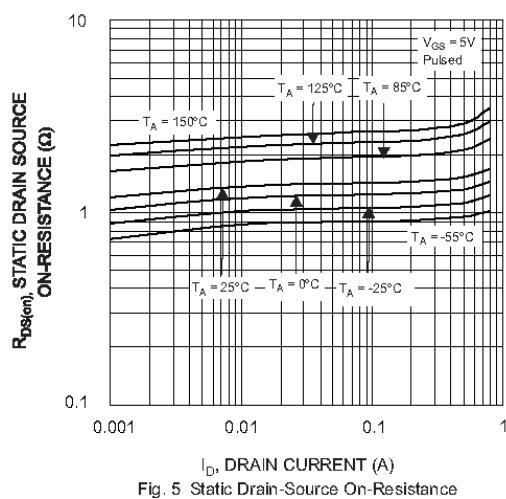


Fig. 5 Static Drain-Source On-Resistance
vs. Drain Current

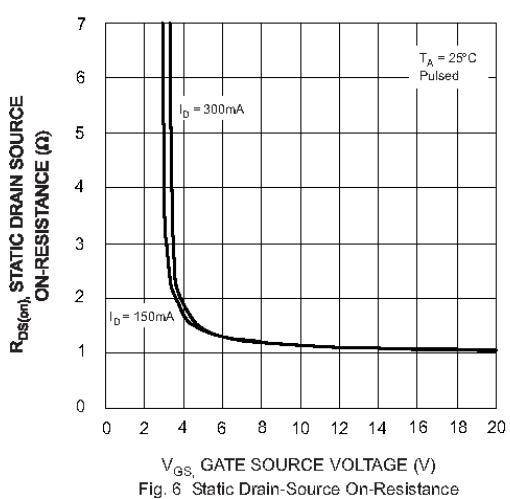
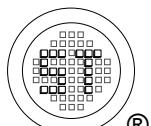


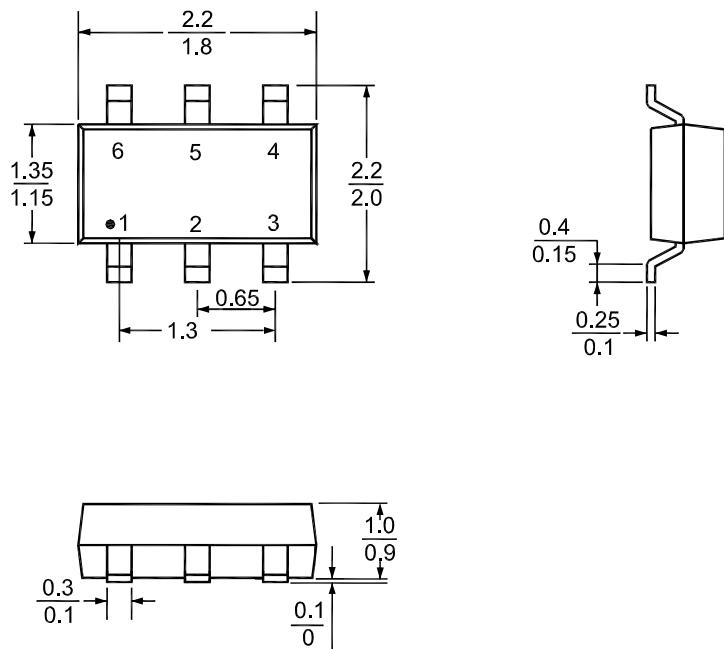
Fig. 6 Static Drain-Source On-Resistance
vs. Gate-Source Voltage



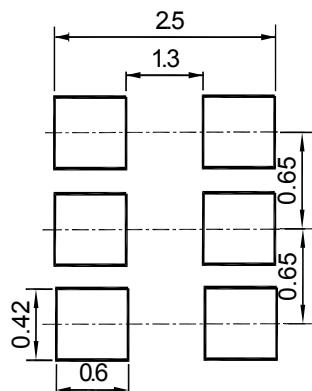
MMBT7002KDW-AH

Package Outline Dimensions (Units: mm)

SOT-363



Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
SOT-363	8	4 ± 0.1	0.157 ± 0.004	178	7	3,000

